

ABSTRACT OF THE DISCLOSURE

A program element has a magnetic layer electrically connected between first and second nodes. At least a portion of the magnetic layer forms a link portion designed to be blown with external laser irradiation.

5 The magnetic layer is provided in the same layer as and with the same structure as a tunneling magneto-resistance element in an MTJ memory cell. An electrical contact between the magnetic layer and respective one of the first and second nodes has the same structure as the electrical contact
10 between the tunneling magneto-resistance element and an interconnection provided in the same metal interconnection layer as respective one of the first and second nodes in the MTJ memory cell.